## NSN 5962-01-213-4587

Memory Microcircuit - Page 1 of 1



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Body Length:1.290 inchesBody Width:0.560 inchesBody Height:0.170 inchesMaximum Power Dissipation Rating:1.0 wattsOperating Tempurature Range:+0.0/+70.0 degrees celsiusStorage Tempurature Range:+0.0/+70.0 degrees celsiusFeatures Provided:Static operation and high performance and programmable and 3-state outputInclosure Material:Ceramic and glassInclosure Configuration:Dual-in-lineOutput Logic Form:N-type metal oxide-semiconductor logicInputTerminal Surface Treatment:SolderVoltage Rating And Type Per Characteristic:-0.5 volts power source and 7.0 volts power sourceTime Rating Per Chacteristic:Er-060 hand pull and err-060 handMemory Device Type:Rom	
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Memory Device Type:	
Rom	
Terminal Type And Quantity:	
24 printed circuit	
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	
Yes - demil/mli	
Fiig:	
A458a0	